

## HEXFRED ULTRAFAST, SOFT RECOVERY DIODE

### **Features**

- Reduced RFI and EMI
- Reduced Snubbing
- Extensive Characterization of Recovery Parameters
- Hermetically Sealed
- Ceramic Eyelets

V <sub>R</sub> = 600V
$V_F = 1.75V$
$Q_{rr} = 380nC$
$di_{(rec)M}/dt = 400A/\mu s$

# Description

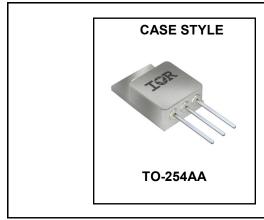
HFA35HB60 is part of the International Rectifier HiRel family of products. These diodes are optimized to reduce losses and EMI/RFI in high frequency power conditioning systems. An extensive characterization of the recovery behavior for different values of current, temperature and di/dt simplifies the calculations of losses in the operating conditions. The softness of the recovery eliminates the need for a snubber in most applications. These devices are ideally suited for power converters, motors drives and other applications where switching losses are significant portion of the total losses.

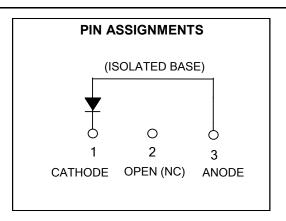
## **Absolute Maximum Ratings**

Characteristics	Max.	Units	
V <sub>R</sub>	D.C. Reverse Voltage	600	V
I <sub>F</sub> @ T <sub>C</sub> = 100°C	Continuous Forward Current ①	22	А
I <sub>FSM</sub> @ T <sub>C</sub> = 25°C	Single Pulse Forward Current ②	225	А
P <sub>D</sub> @ T <sub>C</sub> = 25°C	Maximum Power Dissipation	83	W
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C

#### Notes:

- ① D.C. = 50% rectangle wave
- 2 1/2 sine wave, 60Hz, Pulse Width = 8.33ms







# Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Test Conditions
$V_{BR}$	Cathode Anode Breakdown Voltage	600			V	I <sub>R</sub> = 100μA
V <sub>FM</sub>	Max. Forward Voltage See Fig. 1			1.55		I <sub>F</sub> = 22A, T <sub>J</sub> = -55°C
				1.75	V	I <sub>F</sub> = 22A, T <sub>J</sub> = 25°C
				2.25		I <sub>F</sub> = 45A, T <sub>J</sub> = 25°C
				1.64		I <sub>F</sub> = 22A, T <sub>J</sub> = 125°C
I <sub>RM</sub>	Max. Reverse Leakage Current			10	μA	$V_R = V_R$ Rated
	See Fig. 2			1.0	mA	V <sub>R</sub> = 480V T <sub>J</sub> = 125°C
Ст	Junction Capacitance, See Fig. 3		56	59	pF	V <sub>R</sub> = 200V
Ls	Series Inductance		8.7		nH	Measured from center of bond pad to end of anode bonding wire

# Dynamic Recovery Characteristics @ $T_J = 25$ °C (unless otherwise specified)

	Parameter	Min.	Тур.	Max.	Units	Test Conditions		
t <sub>rr1</sub>	Reverse Recovery Time		60	97	no	T <sub>J</sub> = 25°C	I = 22A	
t <sub>rr2</sub>	See Fig. 5		110	165	ns	T <sub>J</sub> = 125°C	I <sub>F</sub> = 22A	
I <sub>RRM1</sub>	Peak Recovery Current		5.2	11	Α	T <sub>J</sub> = 25°C	V <sub>R</sub> = 200V	
I <sub>RRM2</sub>	See Fig. 6		8.5	13		T <sub>J</sub> = 125°C	V R - 200 V	
Q <sub>rr1</sub>	Reverse Recovery Charge		190	380	nC	T <sub>J</sub> = 25°C	di <sub>f</sub> /dt = 200A/µs	
Q <sub>rr2</sub>	See Fig. 7		560	840	l lic	T <sub>J</sub> = 125°C	αι <sub>f</sub> /αι	
di <sub>(rec)M</sub> /dt1	Peak Rate of Fall of Recovery Current		270	400	A /	T <sub>J</sub> = 25°C		
di <sub>(rec)M</sub> /dt1	During tb - See Fig. 8		170	250	A/μs	T <sub>J</sub> = 125°C		

## **Thermal - Mechanical Characteristics**

	Parameter	Тур.	Max.	Units
$R_{\theta JC}$	Junction-to-Case, Single Leg Conducting		1.5	°C/W
Wt	Weight	9.3		g

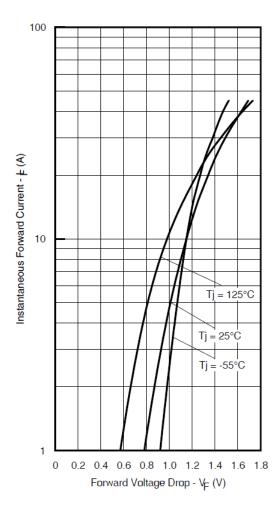


Fig. 1 Typical Forward Voltage Drop Vs. Instantaneous Forward Current

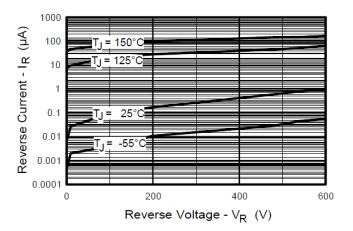


Fig. 2 Typical Values of Reverse Current Vs. Reverse Voltage

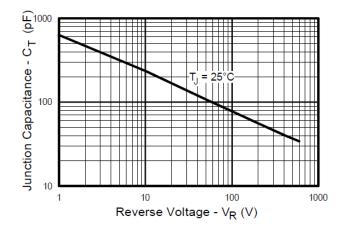


Fig. 3 Typical Junction Capacitance Vs. Reverse Voltage

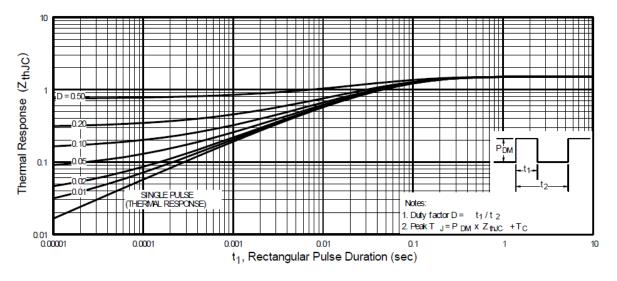


Fig. 4 Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

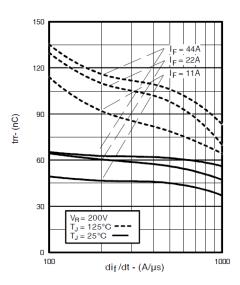


Fig. 5 Typical Reverse Recovery Vs dif/dt

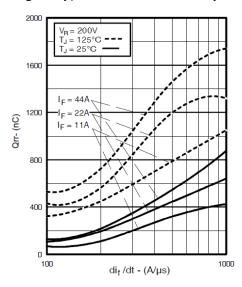


Fig. 7 Typical Stored Charge Vs di<sub>f</sub>/dt

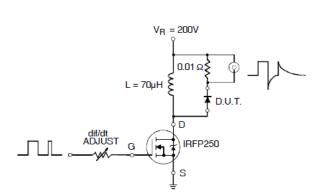


Fig. 9 Typical Reverse Recovery Parameter Test Cir-

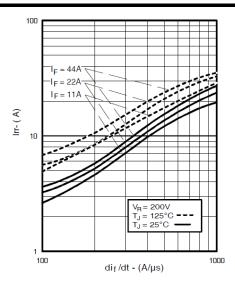


Fig. 6 Typical Recovery Current Vs di<sub>f</sub>/dt

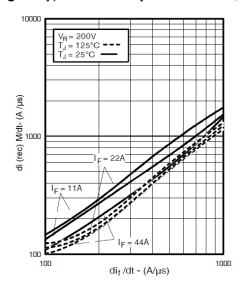
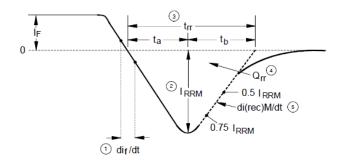


Fig. 8 Typical di<sub>(rec)M</sub>/dt Vs di<sub>f</sub>/dt



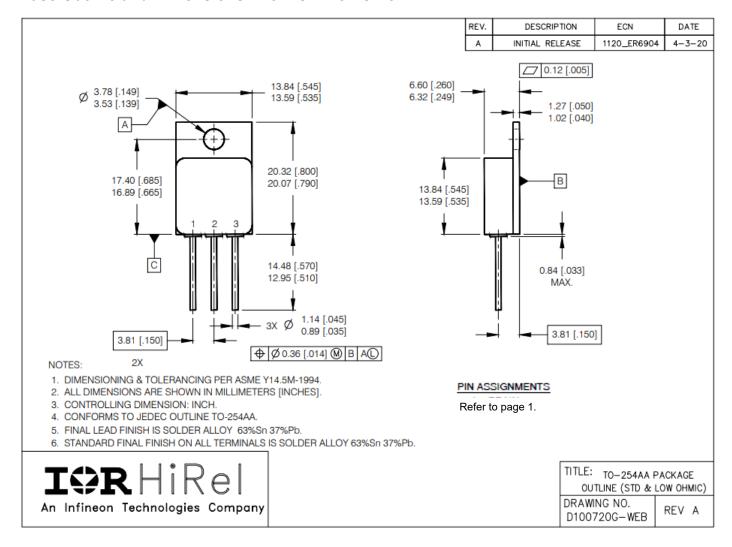
- ② I<sub>RRM</sub> Peak reverse recovery current.
- $^{\circ}$   $t_{rr}$  Reverse recovery time measured from zero crossing point of negative going  $I_F$  to point where a line passing through 0.75 $I_{RRM}$  and 0.5 $I_{RRM}$  extrapolated to zero current.
- $\ \, \oplus \ \, Q_{rr}$  Area under curve defined by  $t_{rr}$  and  $I_{RRM}$   $Q_{rr}$  = ( $t_{rr}$   $_X$   $I_{RRM})$  / 2
- S di<sub>(rec)M</sub>/dt Peak rate of change of current during t<sub>b</sub> position of t<sub>rr</sub>.

Fig. 10 Reverse Recovery Waveform and Definitions



Note: For the most updated package outline, please see the website: TO-254AA

### Case Outline and Dimensions - Low-Ohmic TO-254AA



#### **BERYLLIA WARNING PER MIL-PRF-19500**

Package containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.



www.infineon.com/irhirel

Infineon Technologies Service Center: USA Tel: +1 (866) 951-9519 and International Tel: +49 89 234 65555

Leominster, Massachusetts 01453, USA Tel: +1 (978) 534-5776

San Jose, California 95134, USA Tel: +1 (408) 434-5000

Data and specifications subject to change without notice.



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